

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

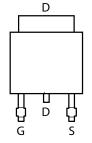
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

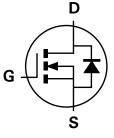
- Case: TO252-3L •
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.33 grams (approximate)



TOP VIEW



PIN OUT -TOP VIEW



Equivalent Circuit

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 3)	Steady State	T _A = 25°C T _A = 85°C	ID	10.0 6.5	А
Pulsed Drain Current (Note 4)			I _{DM}	48	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	PD	1.71	W
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$	R _{0JA}	72.9	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 1. No purposefully added lead.

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
Device mounted on FR-4 PCB, with minimum recommended pad layout.

4. Repetitive rating, pulse width limited by junction temperature.

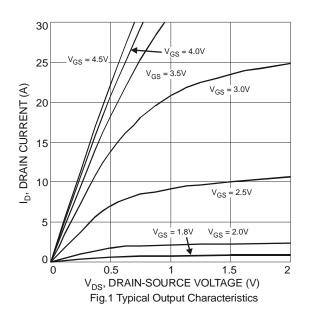


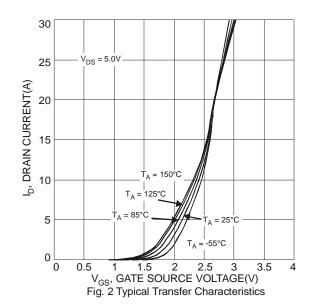
Electrical Characteristics $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	I	-	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V _{GS(th)}	0.8	-	1.6	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		-	12	17 24 mΩ	m O	$V_{GS} = 10V, I_{D} = 9A$	
Static Drain-Source On-Resistance	R _{DS (ON)}		16		11122	$V_{GS} = 4.5V, I_D = 7A$	
Forward Transfer Admittance	Y _{fs}	-	10	-	S	$V_{DS} = 10V, I_{D} = 9A$	
Diode Forward Voltage	V _{SD}	-	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 6)							
Input Capacitance	Ciss	-	798	-	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Output Capacitance	Coss	-	128	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	122	-	pF	1 = 1.00012	
Gate Resistance	Rg	-	1.37	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	-	8.7	-	nC	$V_{GS} = 5V, V_{DS} = 15V,$ $I_{D} = 9A$	
Gate-Source Charge	Q _{gs}	-	1.7	-	nC		
Gate-Drain Charge	Q _{gd}	-	2.4	-	nC		
Turn-On Delay Time	t _{D(on)}	-	5.03	-	ns	$V_{DD} = 15V, V_{GS} = 10V,$ $R_L = 15\Omega, R_G = 6\Omega, I_D = 1A$	
Turn-On Rise Time	tr	-	4.50	-	ns		
Turn-Off Delay Time	t _{D(off)}	-	26.33	-	ns		
Turn-Off Fall Time	t _f	-	8.55	-	ns		

Notes:

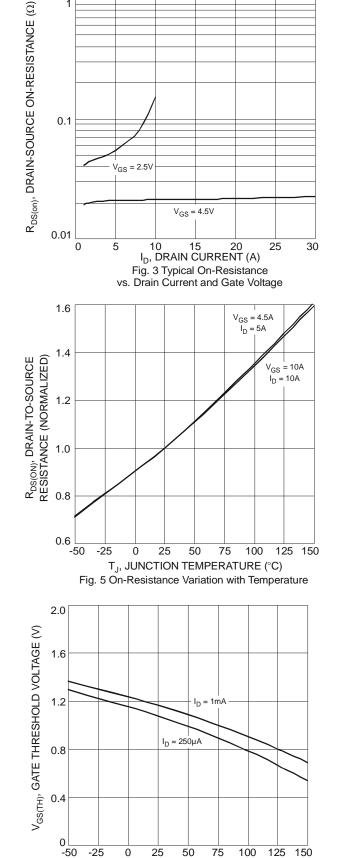
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.





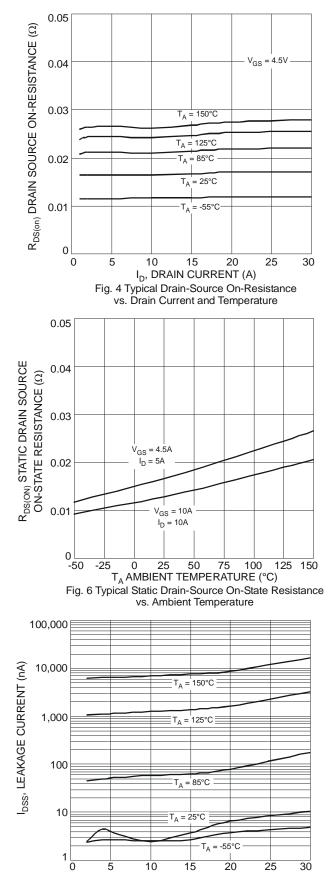


NEW PRODUCT



T_A, AMBIENT TEMPERATURE (°C)

Fig. 7 Gate Threshold Variation vs. Ambient Temperature



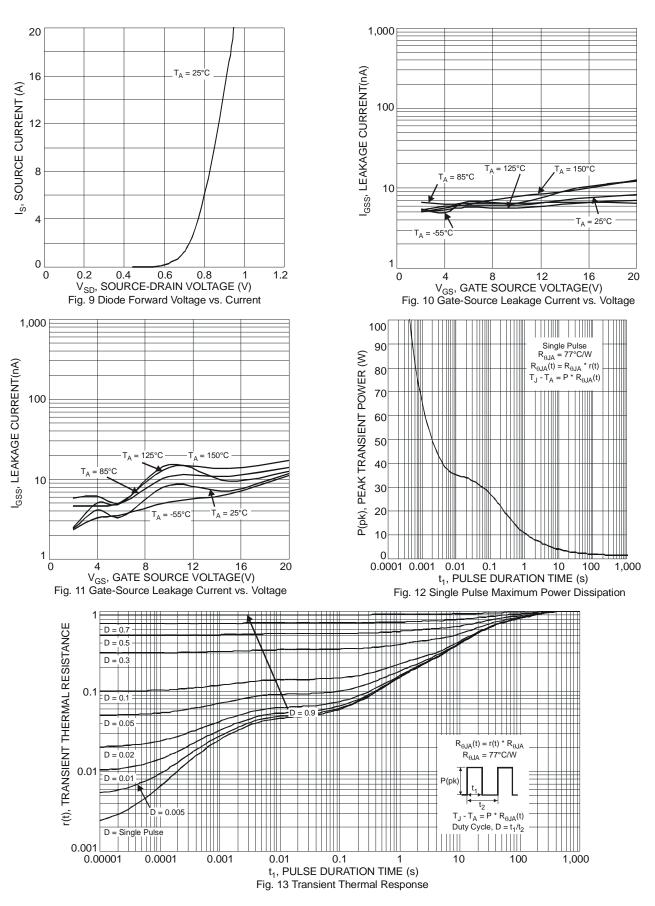
V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Fig. 8 Typical Drain-Source Leakage Current vs Voltage

DMG4800LK3 Document number: DS31959 Rev. 2 - 2









Ordering Information (Note 7)

Part Number	Case	Packaging
DMG4800LK3-13	TO252-3L	2500 / Tape & Reel

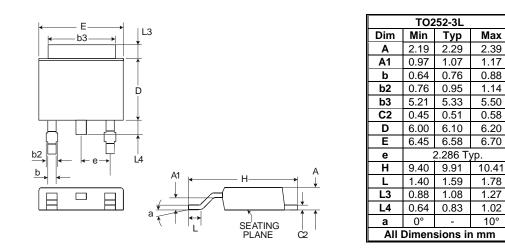
Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

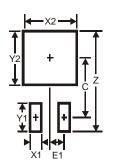


Dil = Manufacturer's Marking N4800L = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01-52)

Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
С	6.9
E1	2.3



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